S/N Unknown **PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Kie Y. Ahn et al.

Examiner:

Unknown

Serial No.:

Unknown

Group Art Unit:

Unknown

Filed:

Herewith

Docket:

303.685US2

Title:

MULTILEVEL COPPER INTERCONNECT WITH DOUBLE PASSIVATION

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

Pursuant to 37 C.F.R. §1.98(d), copies of some of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 09/584157, filed on May 31, 2000, which is relied upon for an earlier filing date under 35 U.S.C. §120.

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial No :Unknown

Filing Date: Herewith

Title: MULTILEVEL COPPER INTERCONNECT WITH DOUBLE PASSIVATION

Page 2 Dkt: 303.685US2

Applicant believes that the U.S. Patent & Trademark Office has waived the requirement

under 37 C.F.R. 1.98 (a)(2)(i) for submitting a copy of each cited U.S. patent and each U.S.

patent application publication. The waiver is provided in a pre-OG notice from the U.S. Patent &

Trademark Office entitled "Information Disclosure Statements May Be Filed Without Copies of

U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003" and

dated July 11, 2003. Applicant acknowledges the requirement to submit copies of foreign patent

documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

The Examiner is invited to contact the Applicants' Representative at the below-listed

telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date of Deposit: November 24, 2003

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to The Commissioner for Patents, Mail Stop Patent Application, P.O. Box 1450, Alexandria, VA 22313-1450.

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE Applicati n Number Unknown STATEMENT BY APPLICANT Even Date Herewith (Use as many sheets as necessary) **Filing Date** First Named Invent r Ahn, Kie **Group Art Unit** Unknown **Examiner Name** Unknown Attorney Docket No: 303.685US2 Sheet 1 of 9

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(Use as many sheets as necessary)	Filing Date	Even Date Herewith		
	First Named Invent r	Ahn, Kie		
	Group Art Unit	Unknown		
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	Group Art Unit	Unknown		
	Examiner Name	Unknown		
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	Group Art Unit	Unknown		
	Examiner Name	Unknown		
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